

(Use several sheets if necessary)

[illegible]

DOCUMENT							TRANSLATION	
DOCUMENT			DATE	COUNTRY	CLASS	SUBCLASS	YES	NO
MG		03/081674 A1	10/2003	WO				
MG		01/93337 A1	12/2001	WO				
		3-88369	04/1991	JP			ABST	
MG		0 241 988 A2	10/1987	EP				
	MG	3-187269	08/1991	JP			ABST	
MG		1 187 218 A2	03/2002	EP				

MG	International Search Report of PCT/GB2004/004722, mailed 31 January 2005
MG	GB Search Report of GB 0326993.3, dated 23 April 2004
MG	LOTT et al, "STRAINED <i>p</i> -CHANNEL InGaSb/AlGaSb MODULATION-DOPED FIELD-EFFECT TRANSISTORS", Electronics Letters, Vol. 28, No. 15, 16 July 1992, Pgs. 1459-1460, XP000307703
MG	Patent Abstracts of Japan, JP 01 009656 A, Vol. 13, No. 184, 12 January 1989
MG	CUI et al., "Technology and First Electrical Characteristics of Complementary NPN and PNP InAlAs/InGaAs Heterojunction Bipolar Transistors", Japanese Journal of Applied Physics, Vol. 41, No. 28, Part 1, February 2002, Pgs. 1124-1130, XP001192196
MG	Patent Abstracts of Japan, JP 63 051678 A, Vol. 012, No. 268, 4 March 1988

03/05/2007

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.